



UNISONIC TECHNOLOGIES CO., LTD

2SB1260

PNP SILICON TRANSISTOR

POWER TRANSISTOR

DESCRIPTION

The UTC 2SB1260 is a epitaxial planar type PNP silicon transistor.

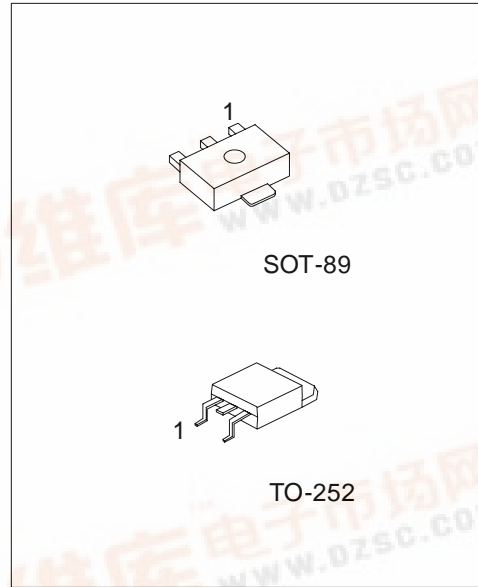
FEATURES

*High breakdown voltage and high current.

$BV_{CEO} = -80V, I_C = -1A$

*Good h_{FE} linearity.

*Low $V_{CE(SAT)}$



*Pb-free plating product number: 2SB1260L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SB1260-x-AB3-R	2SB1260L-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1260-x-TN3-R	2SB1260L-x-TN3-R	TO-252	B	C	E	Tape Reel
2SB1260-x-TN3-T	2SB1260L-x-TN3-T	TO-252	B	C	E	Tube

<p>2SB1260L-x-AB3-R</p>	<p>(1)Packing Type (2)Package Type (3)Rank (4)Lead Plating</p> <p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AB3: SOT-89, TN3: TO-252 (3) refer to Classification of h_{FE} (4) L: Lead Free Plating, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector -Base Voltage	V_{CB0}	-80	V
Collector -Emitter Voltage	V_{CEO}	-80	V
Emitter -Base Voltage	V_{EBO}	-5	V
Peak Collector Current (single pulse, Pw=100ms)	I_{CM}	-2	A
DC Collector Current	I_C	-1	A
Power Dissipation	SOT-89	0.5	W
	TO-252	1.9	W
Operating Temperature	T_J	+150	
Storage Temperature	T_{STG}	-40 ~ +150	

Note 1. Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25 °C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CB0}	$I_C = -50 \mu A$	-80			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA$	-80			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = -50 \mu A$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -60V$			-1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4V$			-1	μA
DC Current Gain(Note 1)	h_{FE}	$V_{CE} = -3V, I_{OUT} = -0.1A$	82		390	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500mA, I_B = -50mA$			-0.4	V
Transition Frequency	f_T	$V_{CE} = -5V, I_E = 50mA, f = 30MHz$		100		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		25		pF

Note 1: Pulse test: $P_w < 300\mu s$, Duty Cycle $< 2\%$

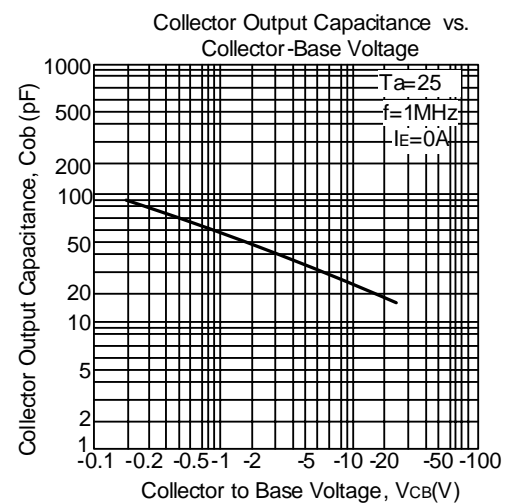
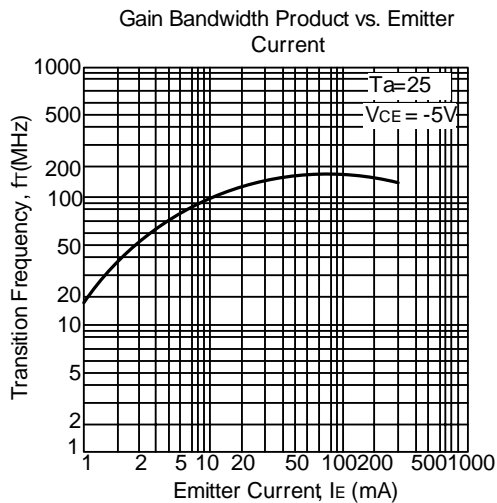
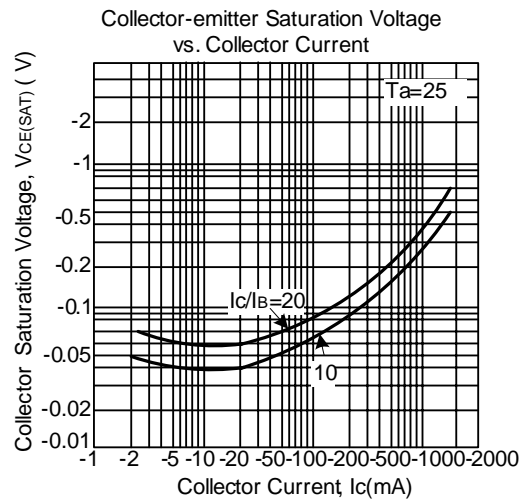
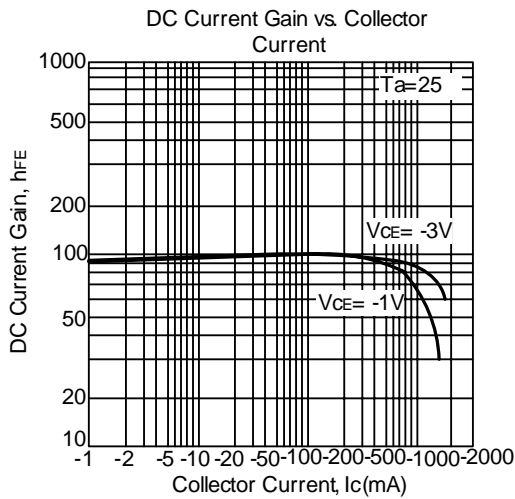
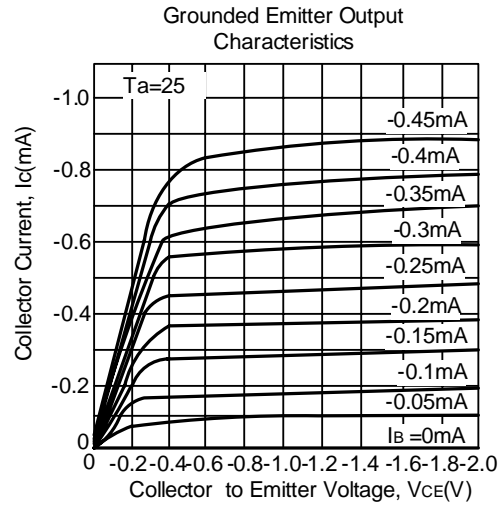
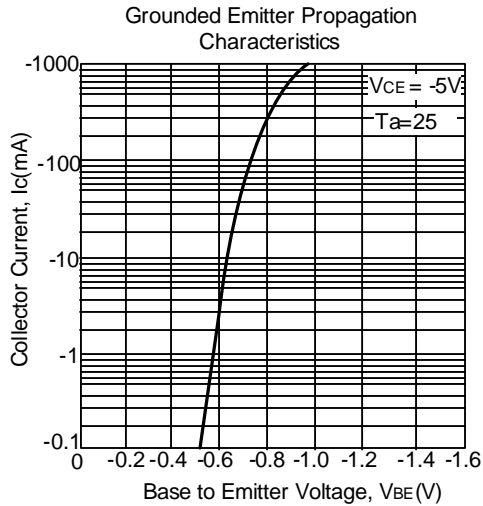
■ CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82 ~ 180	120 ~ 270	180 ~ 390

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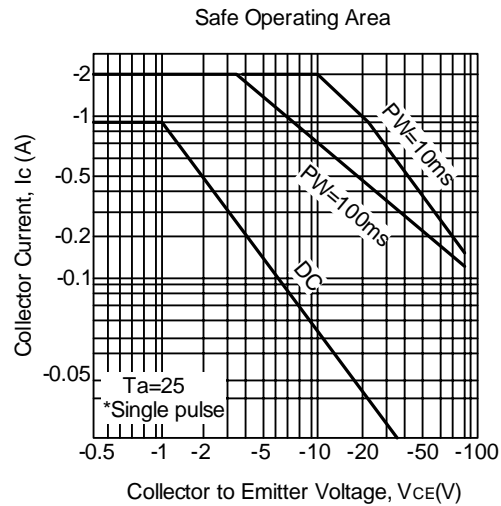
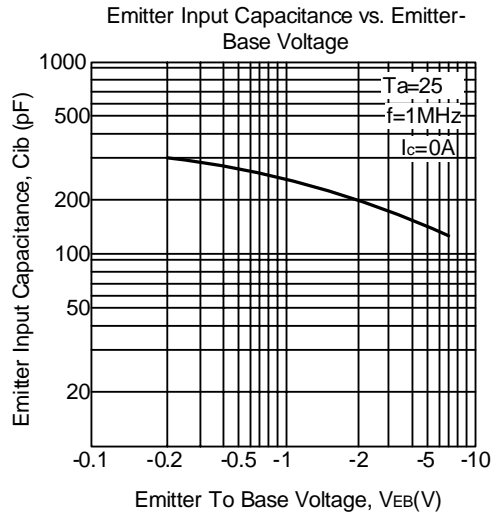
TYPICAL CHARACTERISTICS



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■ TYPICAL CHARACTERISTICS(Cont.)



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